

MOSFETs Silicon N-Channel MOS

### **SSM6N813R**

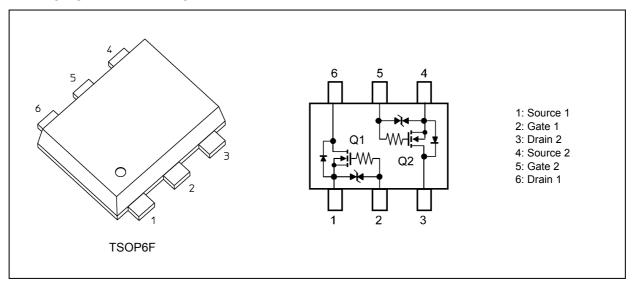
#### 1. Applications

· Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 175 °C MOSFET
- (3) 4.5 V drive
- (4) Low drain-source on-resistance
  - :  $R_{DS(ON)}$  = 110 m $\Omega$  (typ.) (@ $V_{GS}$  = 4.5 V)  $R_{DS(ON)}$  = 88 m $\Omega$  (typ.) (@ $V_{GS}$  = 10 V)

### 3. Packaging and Pin Assignment



### 4. Orderable part number

Orderable part number	AEC-Q101		Note			
SSM6N813R,LF	_		General Use			
SSM6N813R,LXGF	YES	(Note 1)	Unintended Use	(Note 1)		
SSM6N813R,LXHF	YES		Automotive Use			

Note 1: For more information, please contact our sales or use the inquiry form on our website.



### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics				Rating	Unit
Drain-source voltage			$V_{DSS}$	100	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	3.5	Α
Drain current (pulsed)		(Note 1), (Note 2)	I <sub>DP</sub>	7	
Power dissipation		(Note 3)	$P_D$	1.5	W
Power dissipation	(t ≤ 1 s)	(Note 3)		2.5	
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	7.6	mJ
Avalanche current			I <sub>AR</sub>	3.5	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 175°C.
- Note 2: Pulse width (PW)  $\leq$  10  $\mu$ s, duty  $\leq$  1%
- Note 3: Device mounted on an FR4 board. (PD for the entire IC) (FR4, 25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note 4:  $V_{DD}$  = 24 V, Tch = 25 °C (Initial state), L = 1 mH, R<sub>G</sub> = 25  $\Omega$
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±16 V	_	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	_	_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	100	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	80	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	1.5	_	2.5	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 2 A, V <sub>GS</sub> = 4.5 V	_	110	154	mΩ
			I <sub>D</sub> = 3.5 A, V <sub>GS</sub> = 10 V		88	112	

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

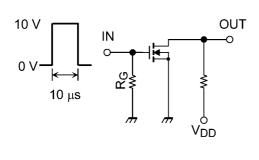
Take this into consideration when using the device.

Note 3: Pulse measurement.

# 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,	_	242	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	7	_	
Output capacitance	C <sub>oss</sub>		_	106		
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 1.0 A,	_	360	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 10 V, $R_G$ = 10 $\Omega$	_	670	_	

#### 6.3. Switching Time Test Circuit



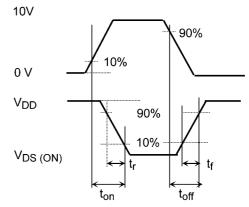


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

# 6.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = 50 \text{ V}, I_D = 2.0 \text{ A},$	_	3.6	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.5 V	_	1.8		
Gate-drain charge	Q <sub>gd</sub>		_	0.9	_	

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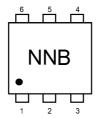


# 6.5. Source-Drain Characteristics (Unless otherwise specified, $T_a$ = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -3.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.9	-1.5	V

Note 1: Pulse measurement.

#### 7. Marking





### 8. Characteristics Curves (Q1,Q2 Common) (Note)

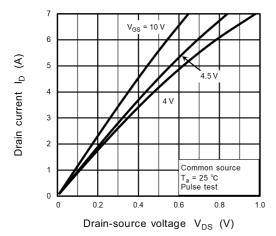


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

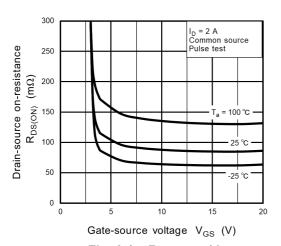


Fig. 8.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

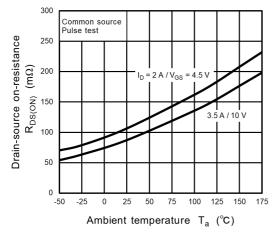


Fig. 8.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

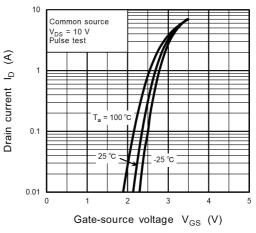


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

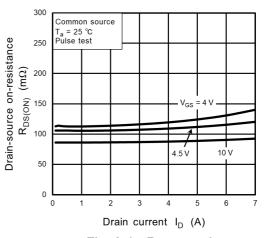


Fig. 8.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

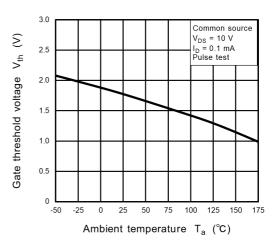


Fig. 8.6 V<sub>th</sub> - T<sub>a</sub>



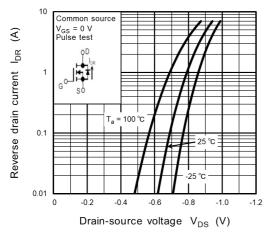


Fig. 8.7 IDR - VDS

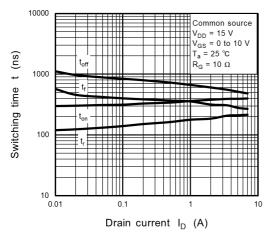


Fig. 8.9 t - I<sub>D</sub>

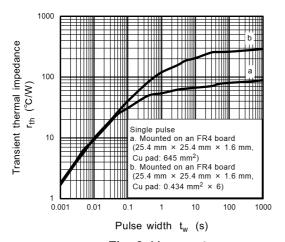


Fig. 8.11 rth - tw

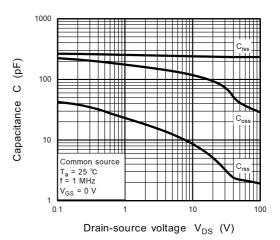


Fig. 8.8 C - V<sub>DS</sub>

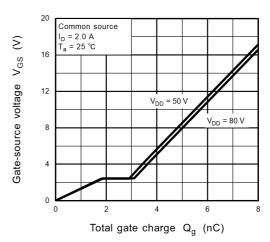


Fig. 8.10 Dynamic Input Characteristics

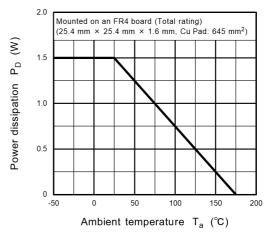


Fig. 8.12 P<sub>D</sub> - T<sub>a</sub>



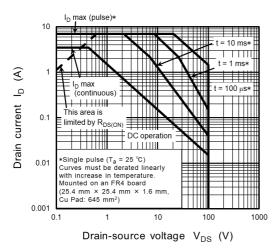


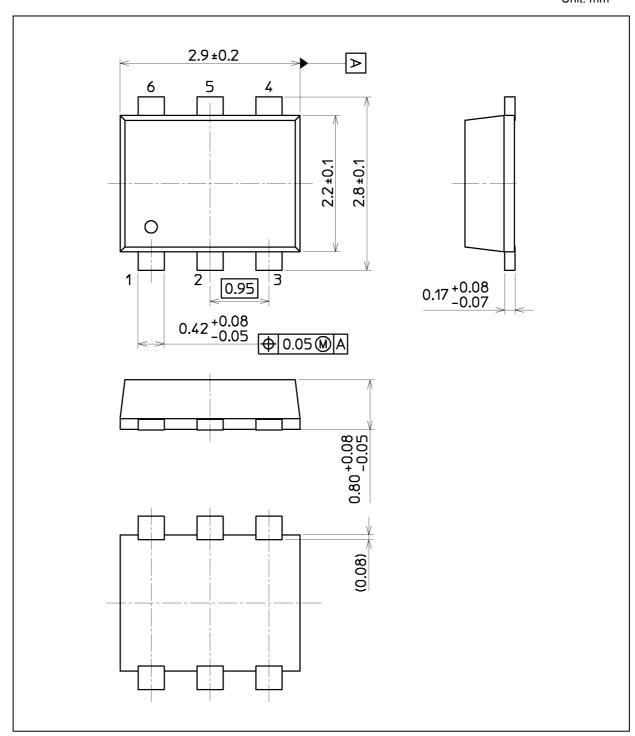
Fig. 8.13 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.016 g (typ.)

Package Name(s)	
TOSHIBA: 2-3AC1A	
Nickname: TSOP6F	

Rev.5.0



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